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converts some of the Si into metal-Si,

wherein said etching comprises selectively etching any unreacted metal, thereby leaving the metal-silicon regions intact,

wherein said depositing comprises performing a blanket deposition of a silicon film, and

wherein said reacting of said silicon cap comprises performing a second RTA to form a metal di-silicide.

D2
27. (Amended) The method of claim 1, wherein said first silicide phase comprises a metal-rich phase.

D4
29. (Amended) The method of claim 4, wherein said first silicide phase comprises a metal-rich phase.

D5
31. (Amended) The method of claim 10, wherein said first silicide phase comprises a metal-rich phase.

D6
33. (Amended) The method of claim 13, wherein said first silicide phase comprises a metal-rich phase.

D7
35. (Amended) The method of claim 25, wherein said first forming silicide phase comprises a metal-rich phase.

REMARKS

Claims 1-8, 10-13 and 23-38 are all the claims presently pending in the application.

Claims 27, 29, 31, 33, 35, and 37 stand rejected upon informalities (e.g., 35 U.S.C. § 112, first paragraph), claims 5-8, 23 and 24 stand rejected upon informalities (e.g., 35 U.S.C. § 112, second paragraph), and claims 1-3, 23, 4-8, 10, 12, 24, 13, 25, 26, 27-30, 31-38 stand rejected on prior art grounds.